

IRF730N

N-channel mosfet transistor



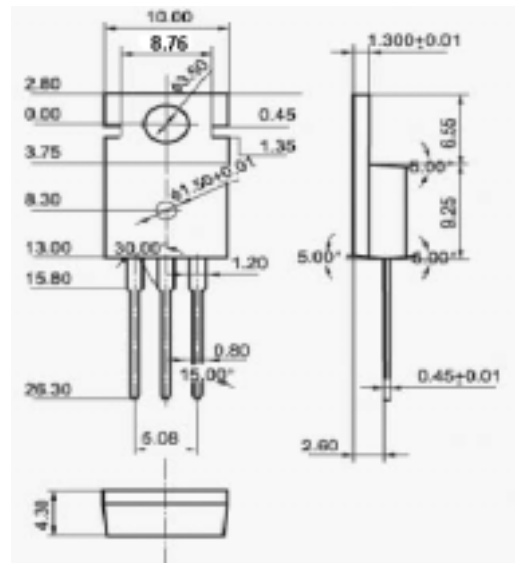
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◆ Features

- With TO-220 package
- Simple drive requirements
- Fast switching
- $V_{DSS}=400V$; $R_{DS(ON)} \leq 1.0 \Omega$; $I_D=5.5A$
- 1.gate 2.drain 3.source

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{DSS}	Drain-source voltage (V _{GS} =0)	400	V
V _{GS}	Gate-source voltage	±20	V
I _D	Drain Current-continuous@ T _C =25°C	5.5	A
P _{tot}	Total Dissipation@T _C =25°C	74	W
T _j	Max. Operating Junction temperature	150	°C
T _{stg}	Storage temperature	-65~150	°C



TO-220

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} =0; I _D =0.25mA	400		V
V _{GS(TH)}	Gate threshold voltage	V _{DS} = V _{GS} ; I _D =0.25mA	2	4	V
R _{DS(ON)}	Drain-source on-stage resistance	V _{GS} =10V; I _D =3.3A		1.0	Ω
I _{GSS}	Gate source leakage current	V _{GS} =±20V;V _{DS} =0		±100	nA
I _{DSS}	Zero gate voltage drain current	V _{DS} =400V; V _{GS} =0		25	uA
V _{SD}	Diode forward voltage	I _F =5.5A; V _{GS} =0		1.6	V